

BGR269

200 MHz, 35 dB gain reverse amplifier Rev. 05 — 30 May 2005

Product data sheet



1.1 General description

High performance amplifier in a SOT115J package, operating at a voltage supply of 24 V (DC).

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Excellent linearity
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability
- 35 dB amplification up to 200 MHz

1.3 Applications

■ Reverse amplifier in two-way CATV systems operating in the 5 MHz to 200 MHz frequency range

1.4 Quick reference data

Table 1: Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|---------------------------|-----------------------|---------------|-----|------|------|
| Gp | power gain | f = 5 MHz | 34.5 | 35 | 35.5 | dB |
| | | f = 200 MHz | 35 | - | 36 | dB |
| I _{tot} | total current consumption | V _B = 24 V | <u>11</u> 145 | 160 | 175 | mA |

[1] The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to $V_B = 35$ V.



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2. Pinning information

Table 2: Pinning

| Pin | Description | Simplified outline | Symbol | | |
|-----|-----------------|--------------------|---------|--|--|
| 1 | input | | | | |
| 2 | common | | 1 5 9 | | |
| 3 | common | 1 3 5 7 9 | | | |
| 5 | +V _B | | 2 3 7 8 | | |
| 7 | common | | sym095 | | |
| 8 | common | | | | |
| 9 | output | | | | |

3. Ordering information

Table 3: Ordering information

| Type number | Package | | | | |
|-------------|---------|---|---------|--|--|
| | Name | Description | Version | | |
| BGR269 | `- | rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads | SOT115J | | |

4. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|------------|-----|------|------|
| Vi | RF input voltage | | - | 50 | dBmV |
| T _{mb} | mounting base temperature | е | -20 | +100 | °C |
| T _{stg} | storage temperature range | | -40 | +100 | °C |

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5. Characteristics

Table 5: Characteristics

Bandwidth 5 MHz to 200 MHz; $V_B = 24 \text{ V}$; $T_{mb} = 30 \,^{\circ}\text{C}$; $Z_S = Z_L = 75 \,\Omega$; unless otherwise specified.

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------|--------------------------------|--|------------|------|-----|------|------|
| G_p | power gain | f = 5 MHz | | 34.5 | 35 | 35.5 | dB |
| | | f = 200 MHz | | 35 | - | 36 | dB |
| SL | slope straight line | f = 5 MHz to 200 MHz | | 0 | - | 0.6 | dB |
| FL | flatness of frequency response | f = 5 MHz to 10 MHz | | -0.1 | - | +0.4 | dB |
| | | f = 10 MHz to 190 MHz | | -0.1 | - | +0.5 | dB |
| | | f = 190 MHz to 200 MHz | | -0.1 | - | +0.4 | dB |
| S ₁₁ | input return losses | f = 5 MHz to 200 MHz | | 20 | - | - | dB |
| S ₂₂ | output return losses | f = 5 MHz to 200 MHz | | 20 | - | - | dB |
| φ _{s21} | phase response | f = 5 MHz | | -45 | - | +45 | deg |
| S ₁₂ | reverse isolation | f = 5 MHz to 200 MHz | | - | - | -42 | dB |
| СТВ | composite triple beat | $V_0 = 50 \text{ dBmV}$ | | | | | |
| | | 6 channels flat; measured at 37 MHz | <u>[1]</u> | - | - | -74 | dB |
| | | 10 channels flat; measured at 67.25 MHz | [2] | - | - | -68 | dB |
| | | 28 channels flat; measured at 199.25 MHz | [3] | - | - | -57 | dB |
| X _{mod} | cross modulation | $V_0 = 50 \text{ dBmV}$ | | | | | |
| | | 6 channels flat; measured at 37 MHz | <u>[1]</u> | - | - | -66 | dB |
| | | 10 channels flat; measured at 25 MHz | [2] | - | - | -57 | dB |
| | | 28 channels flat; measured at 25 MHz | [3] | - | - | -50 | dB |
| CSO | composite second order | $V_0 = 50 \text{ dBmV}$ | | | | | |
| | distortion | 6 channels flat; measured at 38 MHz | <u>[1]</u> | - | - | -74 | dB |
| | | 10 channels flat; measured at 68.5 MHz | [2] | - | - | -74 | dB |
| | | 28 channels flat; measured at 200.5 MHz | [3] | - | - | -66 | dB |
| Vo | output voltage | $d_{im} = -60 \text{ dB}$ | [4] | 62 | - | - | dBmV |
| d ₂ | second order distortion | | [5] | - | - | -70 | dB |
| NF | noise figure | f = 70 MHz | | - | - | 5.3 | dB |
| | | f = 200 MHz | | - | - | 5.5 | dB |
| I _{tot} | total current consumption | | [6] | 145 | 160 | 175 | mA |

^[1] From the following frequencies: 7.00 MHz, 13.00 MHz, 19.00 MHz, 25.00 MHz, 31.00 MHz and 37.00 MHz.

- [4] Measured according to DIN45004B;
 - $f_p = 197.25 \; \text{MHz}; \; V_p = V_o; \; f_q = 204.25 \; \text{MHz}; \; V_q = V_o 6 \; \text{dB}; \; f_r = 206.25 \; \text{MHz}; \; V_r = V_o 6 \; \text{dB}; \; \text{measured at} \; f_p + f_q f_r = 195.25 \; \text{MHz}.$
- [5] $f_p = 83.25 \text{ MHz}$; $V_p = 50 \text{ dBmV}$; $f_q = 115.25 \text{ MHz}$; $V_q = 50 \text{ dBmV}$; measured at $f_p + f_q = 198.5 \text{ MHz}$.
- [6] The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to $V_B = 35$ V.

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^[2] From the following frequencies: 7.00 MHz, 13.00 MHz, 19.00 MHz, 25.00 MHz, 31.00 MHz, 37.00 MHz, 43.00 MHz, 55.25 MHz, 61.25 MHz and 67.25 MHz.

^[3] From the following frequencies: 7.00 MHz, 13.00 MHz, 19.00 MHz, 25.00 MHz, 31.00 MHz, 37.00 MHz, 43.00 MHz, 55.25 MHz, 61.25 MHz, 67.25 MHz, 77.25 MHz, 83.25 MHz, 109.25 MHz, 115.25 MHz, 121.25 MHz, 127.25 MHz, 133.25 MHz, 139.25 MHz, 145.25 MHz, 151.25 MHz, 157.25 MHz, 163.25 MHz, 169.25 MHz, 175.25 MHz, 181.25 MHz, 187.25 MHz, 193.25 MHz and 199.25 MHz.

6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

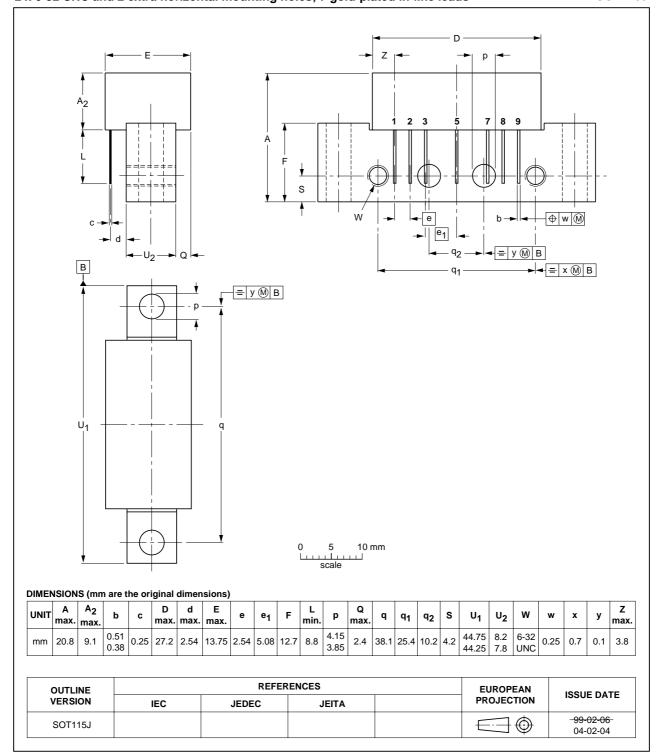


Fig 1. Package outline SOT115J

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7. Revision history

Table 6: Revision history

| Document ID | Release date | Data sheet status | Change notice | Doc. number | Supersedes |
|----------------|--------------|---|---------------|--------------------|------------------|
| BGR269_5 | 20050530 | Product data sheet | - | 9397 750 14741 | BGR269_4 |
| Modifications: | | t of this data sheet has been standard of Philips Semic | | omply with the new | presentation and |
| BGR269_4 | 20020305 | Product specification | - | 9397 750 09455 | BGR269_N_3 |
| BGR269_N_3 | 20010928 | Preliminary specification | - | 9397 750 08867 | BGR269_N_2 |
| BGR269_N_2 | 20001212 | Preliminary specification | - | 9397 750 07841 | BGR269_1 |
| BGR269_1 | 20000501 | Objective specification | - | 9397 750 07043 | - |

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8. Data sheet status

| Level | Data sheet status [1] | Product status [2] [3] | Definition |
|-------|-----------------------|------------------------|--|
| I | Objective data | Development | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice. |
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- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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